

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
200V	0.16Ω@10V	18A



合肥矽普半导体

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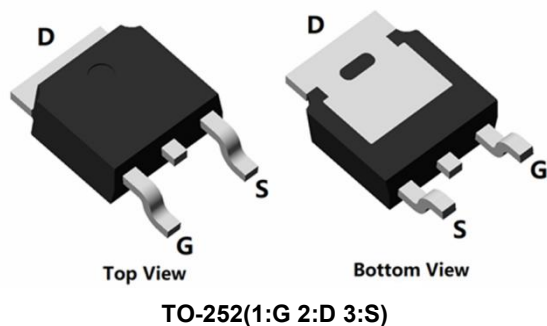
Feature

- Fast Switching
- Low Gate Charge and $R_{DS(on)}$
- 100% Single Pulse avalanche energy Test

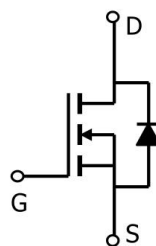
Applications

- DC-DC Converter
- Ideal for high-frequency switching and synchronous rectification

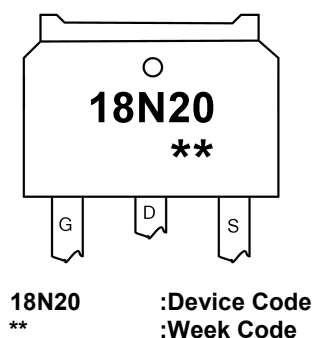
Package



Circuit diagram



Marking



Order Information

Device	Package	Unit/Tape
SP18N20TH	TO-252	2500

Absolute maximum ratings (Ta=25°C, unless otherwise noted)

Parameter	Symbol	Rating	Units
Drain-Source Voltage	V_{DS}	200	V
Gate-Source Voltage	V_{GS}	± 30	V
Continuous Drain Current ($T_C=25^\circ\text{C}$)	I_D	18	A
Continuous Drain Current ($T_C=100^\circ\text{C}$)	I_D	12	A
Pulsed Drain Current	I_{DM}	72	A
Single Pulse Avalanche Energy ¹	E_{AS}	180	mJ
Power Dissipation ($T_C=25^\circ\text{C}$)	P_D	130	W
Thermal Resistance Junction-to-Case	$R_{\theta JC}$	0.96	$^\circ\text{C/W}$
Storage Temperature Range	T_{STG}	-55 to 150	$^\circ\text{C}$
Operating Junction Temperature Range	T_J	-55 to 150	$^\circ\text{C}$

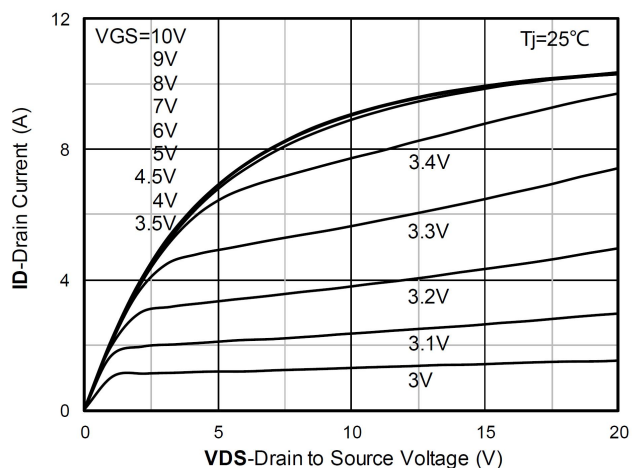
Electrical characteristics (Ta=25°C, unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	VGS=0V , ID=250uA	200	-	-	V
Drain-Source Leakage Current	IDSS	VDS=160V , VGS=0V , TJ=25℃	-	-	25	uA
Gate-Source Leakage Current	IGSS	VGS=±30V , VDS=0V	-	-	±100	nA
Gate Threshold Voltage	VGS(th)	VGS=VDS , ID =250uA	2	3	4	V
Static Drain-Source On-Resistance	RDS(ON)	VGS=10V , ID=6A	-	0.16	0.2	Ω
Dynamic characteristics						
Input Capacitance	Ciss	VDS=25V , VGS=0V , f=1MHz	-	1133	-	pF
Output Capacitance	Coss		-	183	-	
Reverse Transfer Capacitance	Crss		-	52	-	
Total Gate Charge	Qg	VDS=160V , VGS=10V , ID=11A	-	64	-	nC
Gate-Source Charge	Qgs		-	11	-	
Gate-Drain Charge	Qgd		-	31	-	
Switching Characteristics						
Turn-On Delay Time	Td(on)	VDD=100V VGS=10V , RG=2.5Ω, ID=11A	-	11	-	nS
Rise Time	Tr		-	18	-	
Turn-Off Delay Time	Td(off)		-	25	-	
Fall Time	Tf		-	6	-	
Diode Characteristics						
Diode Forward Voltage	VSD	VGS=0V , IS=1A , TJ=25℃	-	-	1.2	V
Maximum Body-Diode Continuous Current	IS		-	-	18	A
Reverse Recovery Time	Trr	IS=18A, di/dt=100A/us, TJ=25℃	-	160	-	nS
Reverse Recovery Charge	Qrr		-	880	-	nC

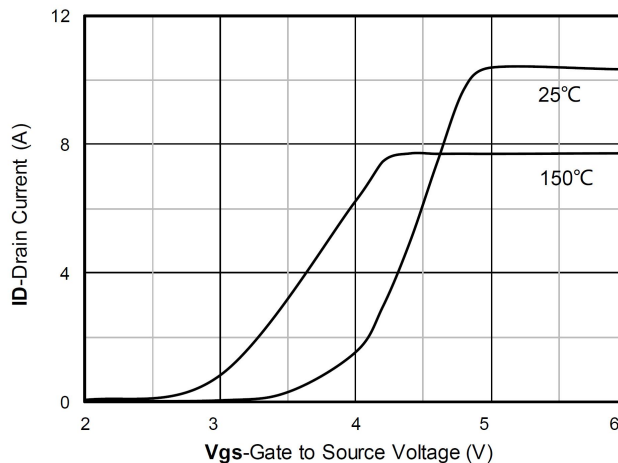
Note :

- The EAS test condition is $V_{DD}=50V, V_{GS}=10V, L=10mH, R_G=25\Omega$

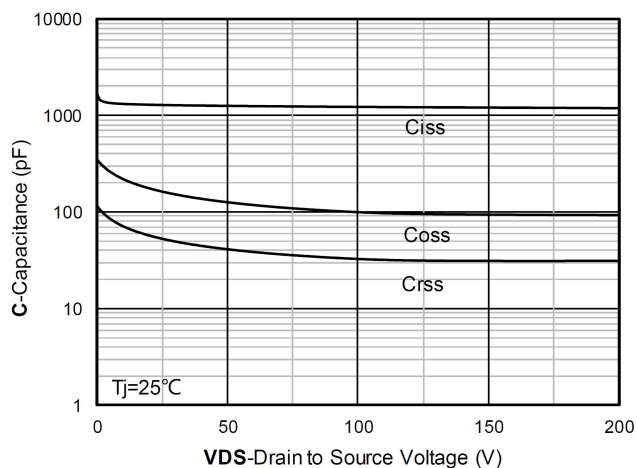
Typical Characteristics



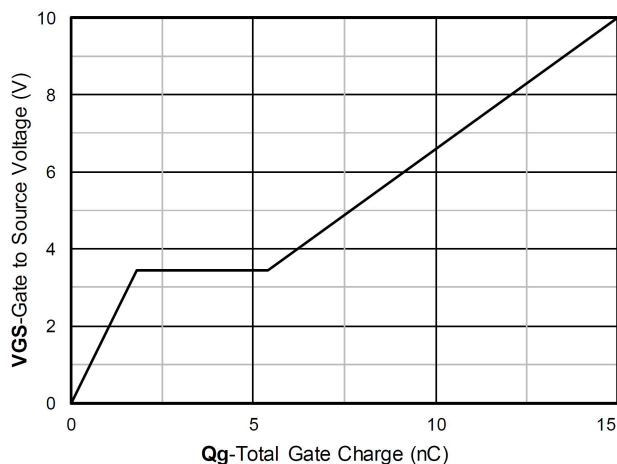
Output Characteristics



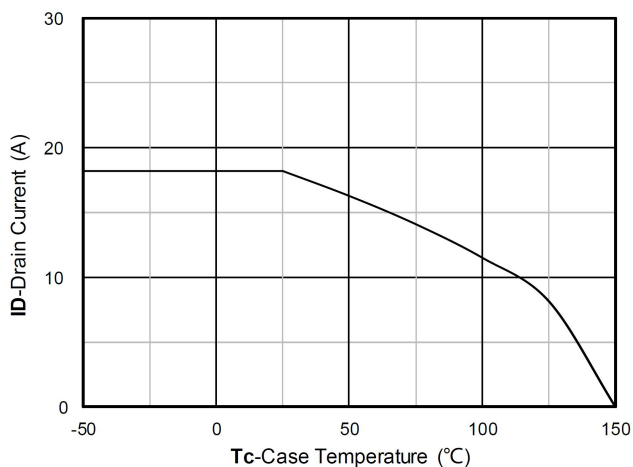
Transfer Characteristics



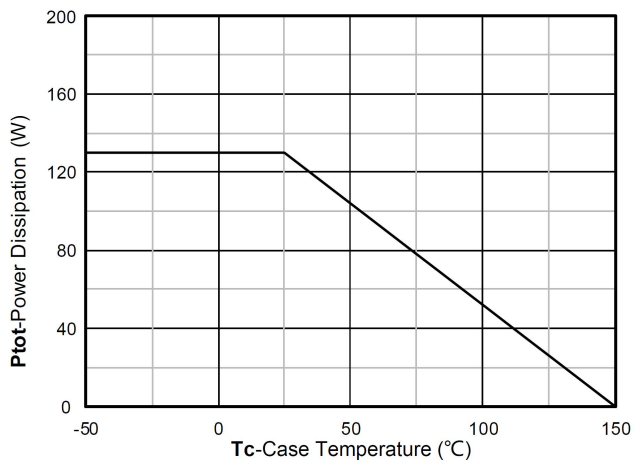
Capacitance Characteristics



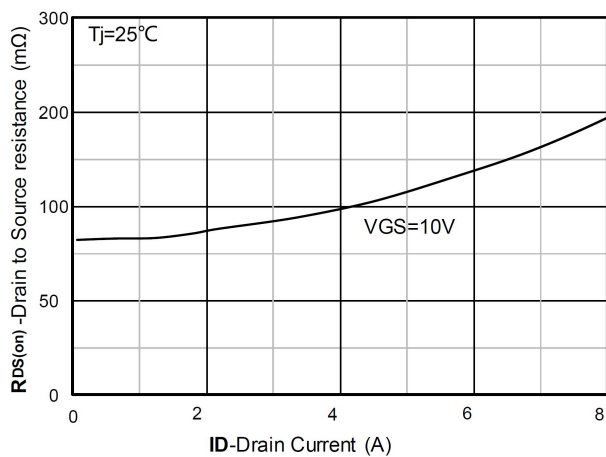
Gate Charge



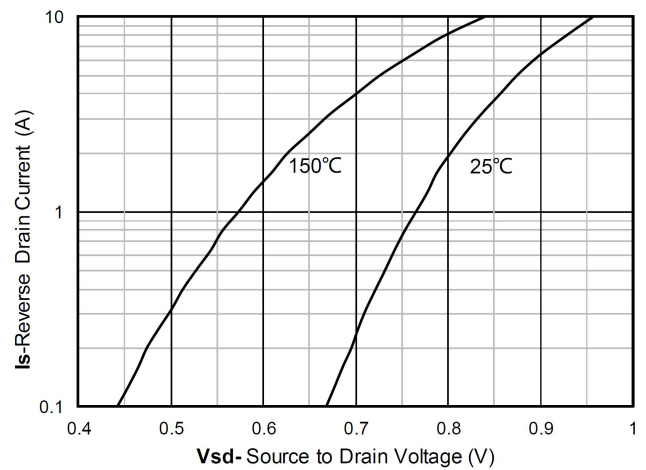
Current dissipation



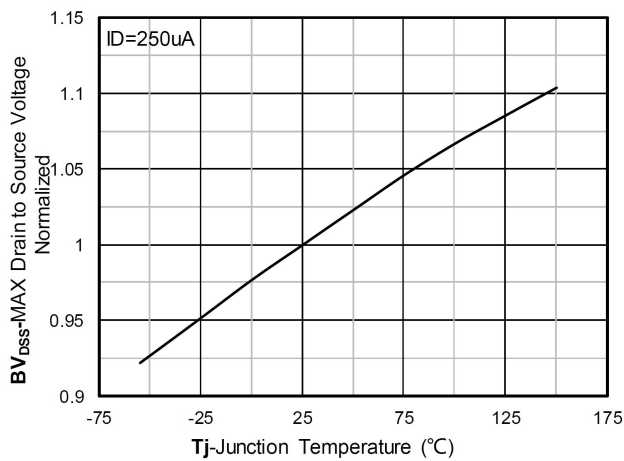
Power dissipation



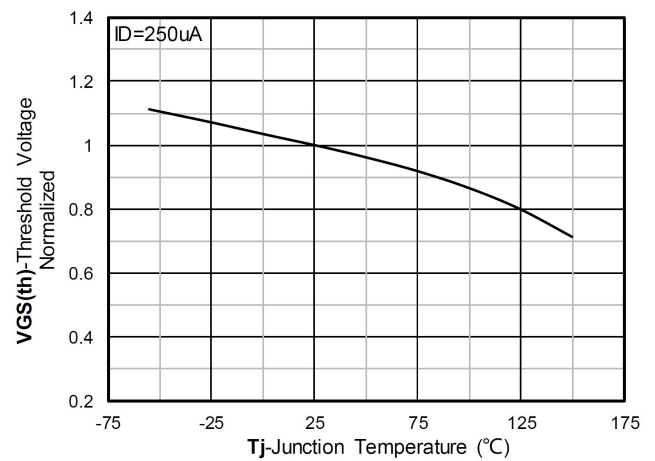
RDS(on) VS Drain Current



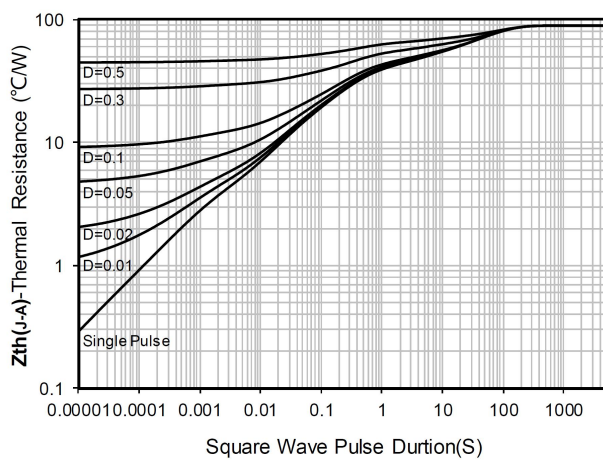
Forward characteristics of reverse diode



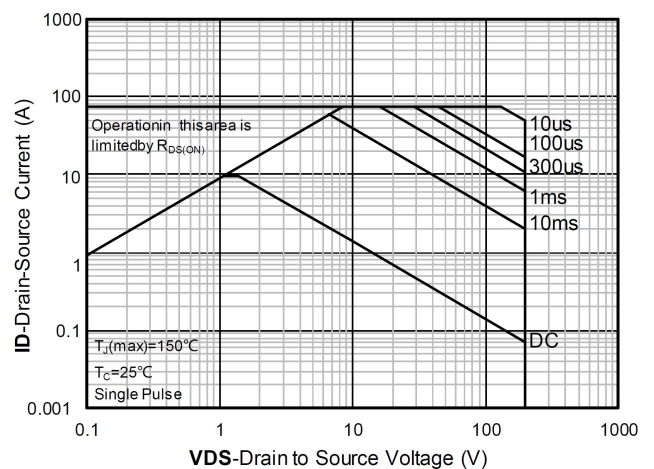
Normalized breakdown voltage



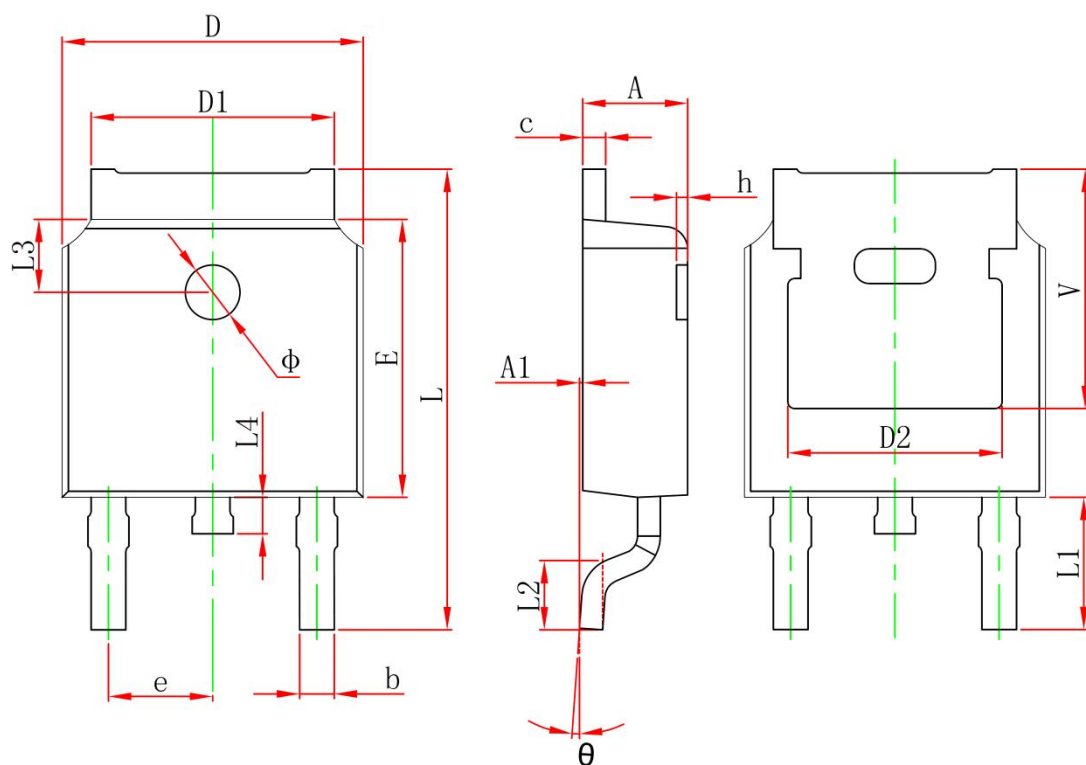
Normalized Threshold voltage



Maximum Transient Thermal Impedance



Safe Operation Area

TO-252 Package Information


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 REF.		0.190 REF.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 REF.		0.114 REF.	
L2	1.400	1.700	0.055	0.067
L3	1.600 REF.		0.063 REF.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 REF.		0.211 REF.	